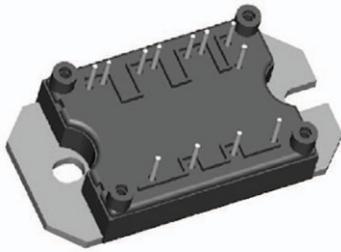


## “Half Bridge” IGBT MTP (Warp Speed IGBT), 114 A


**MTP**

### FEATURES

- Gen 4 warp speed IGBT technology
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery
- Very low conduction and switching losses
- Optional SMD thermistor (NTC)
- Very low junction to case thermal resistance
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**

### PRODUCT SUMMARY

$V_{CES}$	600 V
$V_{CE(on)}$ typical at $V_{GE} = 15$ V	2.3 V
$I_C$ at $T_C = 25$ °C	114 A
Speed	30 kHz to 100 kHz
Package	MTP
Circuit	Half bridge

### BENEFITS

- Optimized for welding, UPS and SMPS applications
- Low EMI, requires less snubbing
- Direct mounting to heatsink
- PCB solderable terminals
- Very low stray inductance design for high speed operation

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		600	V
Continuous collector current	$I_C$	$T_C = 25$ °C	114	A
		$T_C = 109$ °C	50	
Pulsed collector current	$I_{CM}$		350	
Peak switching current	$I_{LM}$		350	
Diode continuous forward current	$I_F$	$T_C = 109$ °C	34	
Peak diode forward current	$I_{FM}$		200	
Gate to emitter voltage	$V_{GE}$		± 20	
RMS isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1$ min	2500	
Maximum power dissipation	$P_D$	$T_C = 25$ °C	658	W
		$T_C = 100$ °C	263	



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$	600	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 50\text{ A}$	-	2.3	3.15	V
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$	-	2.5	3.2	
		$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	1.72	2.17	
Gate threshold voltage	$V_{GE(th)}$	$I_C = 0.5\text{ mA}$	3	-	6	
Collector to emitter leaking current	$I_{CES}$	$V_{GE} = 0\text{ V}, I_C = 600\text{ A}$	-	-	0.4	mA
		$V_{GE} = 0\text{ V}, I_C = 600\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	-	10	
Diode forward voltage drop	$V_{FM}$	$I_F = 50\text{ A}, V_{GE} = 0\text{ V}$	-	1.58	1.80	V
		$I_F = 50\text{ A}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	1.49	1.68	
		$I_F = 100\text{ A}, V_{GE} = 0\text{ V}, T_J = 25\text{ }^\circ\text{C}$	-	1.9	2.17	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 250$	nA

<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	$Q_g$	$I_C = 52\text{ A}$ $V_{CC} = 400\text{ V}$ $V_{GE} = 15\text{ V}$	-	331	385	nC
Gate to emitter charge (turn-on)	$Q_{ge}$		-	44	52	
Gate to collector charge (turn-on)	$Q_{gc}$		-	133	176	
Turn-on switching loss	$E_{on}$	Internal gate resistors (see electrical diagram) $I_C = 50\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}, L = 200\text{ }\mu\text{H}$ Energy losses include tail and diode reverse recovery, $T_J = 25\text{ }^\circ\text{C}$	-	0.26	-	mJ
Turn-off switching loss	$E_{off}$		-	1.2	-	
Total switching loss	$E_{ts}$		-	1.46	-	
Turn-on switching loss	$E_{on}$	Internal gate resistors (see electrical diagram) $I_C = 50\text{ A}, V_{CC} = 480\text{ V}, V_{GE} = 15\text{ V}, L = 200\text{ }\mu\text{H}$ Energy losses include tail and diode reverse recovery, $T_J = 150\text{ }^\circ\text{C}$	-	0.73	-	mJ
Turn-off switching loss	$E_{off}$		-	1.66	-	
Total switching loss	$E_{ts}$		-	2.39	-	
Input capacitance	$C_{ies}$	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1.0\text{ MHz}$	-	7100	-	pF
Output capacitance	$C_{oes}$		-	510	-	
Reverse transfer capacitance	$C_{res}$		-	140	-	
Diode reverse recovery time	$t_{rr}$	$V_{CC} = 200\text{ V}, I_C = 50\text{ A}$ $dI/dt = 200\text{ A}/\mu\text{s}$	-	82	97	ns
Diode peak reverse current	$I_{rr}$		-	8.3	10.6	A
Diode recovery charge	$Q_{rr}$		-	340	514	nC
Diode reverse recovery time	$t_{rr}$	$V_{CC} = 200\text{ V}, I_C = 50\text{ A}$ $dI/dt = 200\text{ A}/\mu\text{s}$ $T_J = 125\text{ }^\circ\text{C}$	-	137	153	ns
Diode peak reverse current	$I_{rr}$		-	12.7	14.8	A
Diode recovery charge	$Q_{rr}$		-	870	1132	nC



THERMISTOR SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Resistance	$R_0$ <sup>(1)</sup>	$T_0 = 25\text{ }^\circ\text{C}$	-	30	-	k $\Omega$
Sensitivity index of the thermistor material	$\beta$ <sup>(1)(2)</sup>	$T_0 = 25\text{ }^\circ\text{C}$ $T_1 = 85\text{ }^\circ\text{C}$	-	4000	-	K

**Notes**

(1)  $T_0, T_1$  are thermistor's temperatures

(2)  $\frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$ , temperature in Kelvin

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	IGBT, Diode		-40	-	150	°C
	Thermistor					
Storage temperature range	$T_{Stg}$		-40	-	125	
Junction to case	IGBT		-	-	0.38	°C/W
	Diode					
Case to sink per module	$R_{thCS}$	Heatsink compound thermal conductivity = 1 W/mK	-	0.06	-	
Clearance <sup>(1)</sup>		External shortest distance in air between 2 terminals	5.5	-	-	mm
Creepage <sup>(1)</sup>		Shortest distance along the external surface of the insulating material between 2 terminals	8	-	-	
Mounting torque to heatsink		A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	3 ± 10 %			Nm
Weight			66			g

**Note**

(1) Standard version only i.e. without optional thermistor

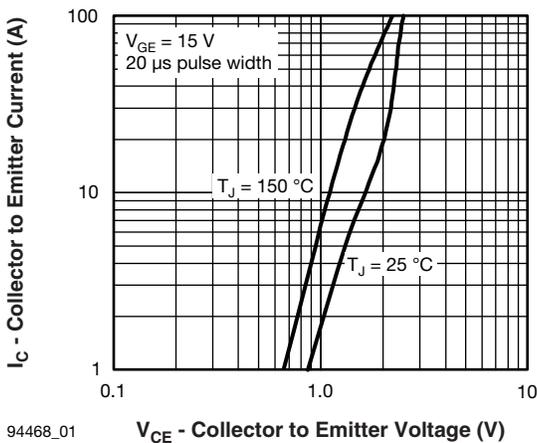


Fig. 1 - Typical Output Characteristics

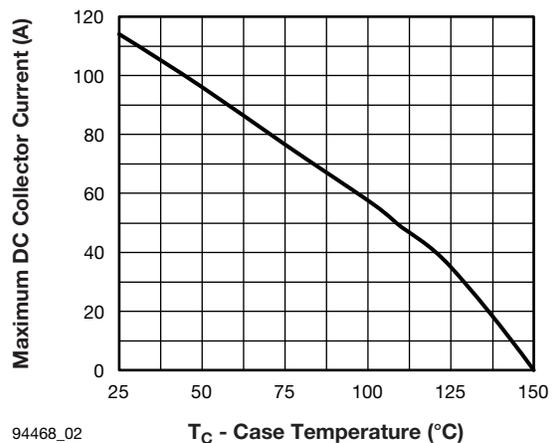
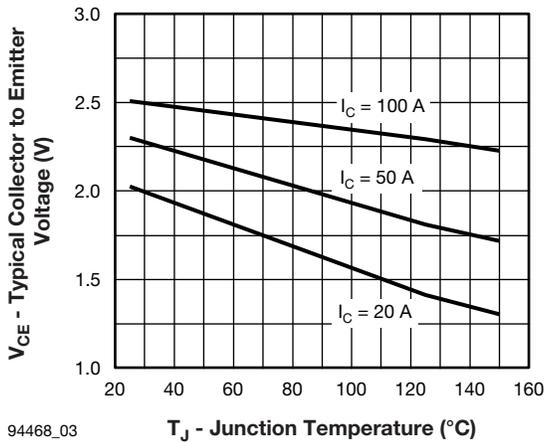
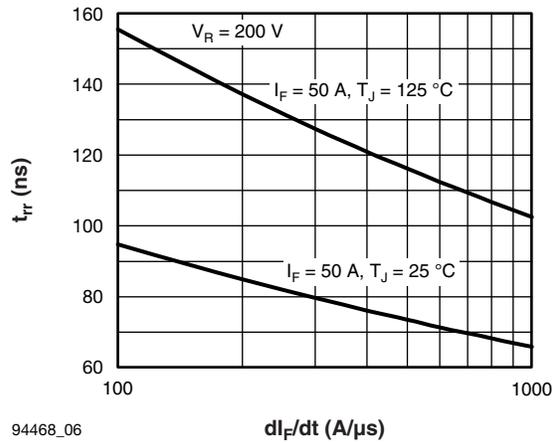


Fig. 2 - Maximum Collector Current vs. Case Temperature



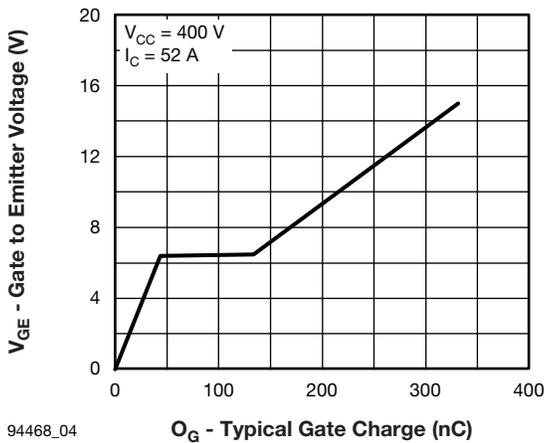
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Fig. 3 - Typical Collector to Emitter Voltage vs. Junction Temperature



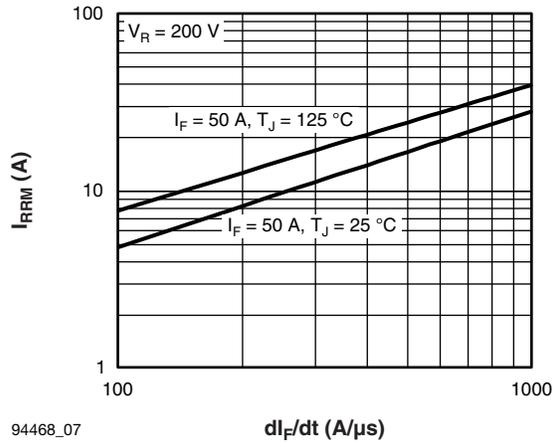
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Fig. 6 - Typical Reverse Recovery Time vs.  $di_F/dt$



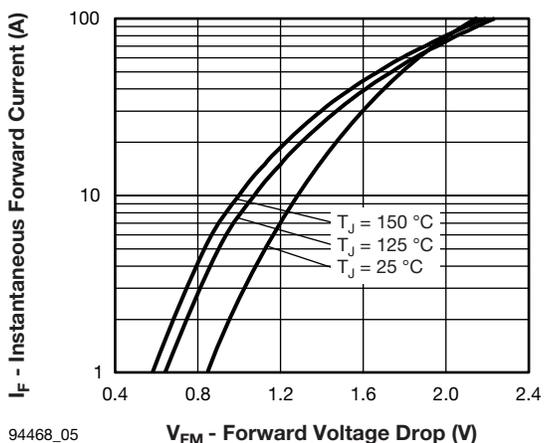
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Fig. 4 - Typical Gate Charge vs. Gate to Emitter Voltage



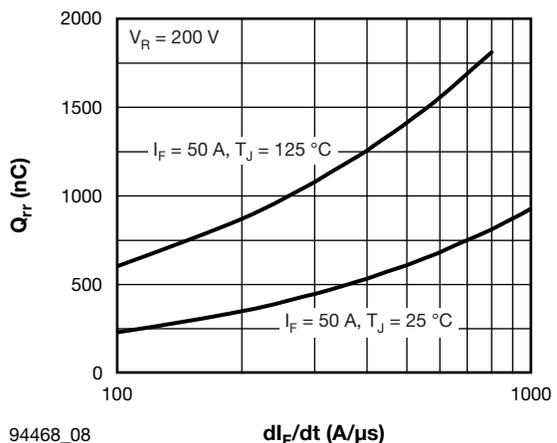
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Fig. 7 - Typical Reverse Recovery Current vs.  $di_F/dt$



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Fig. 5 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current



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Fig. 8 - Typical Stored Charge vs.  $di_F/dt$

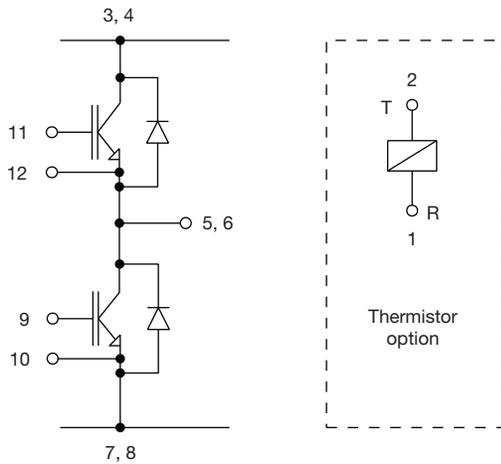


Fig. 9 - Functional Diagram

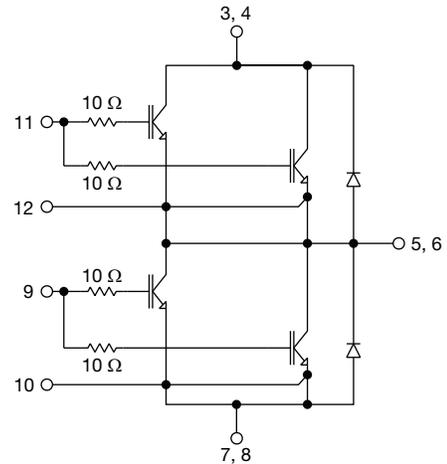
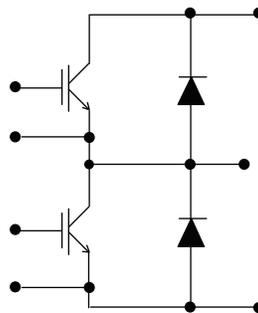


Fig. 10 - Electrical Diagram

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>50</b>	<b>MT</b>	<b>060</b>	<b>W</b>	<b>H</b>	<b>T</b>	<b>A</b>	<b>PbF</b>
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating (50 = 50 A)
- 3** - Essential part number
- 4** - Voltage rating (060 = 600 V)
- 5** - Speed/type (W = Warp IGBT)
- 6** - Circuit configuration (H = Half bridge)
- 7** - T = Thermistor
- 8** - A = Al<sub>2</sub>O<sub>3</sub> substrate
- 9** - Lead (Pb)-free

**CIRCUIT CONFIGURATION**

**LINKS TO RELATED DOCUMENTS**

Dimensions	<a href="http://www.vishay.com/doc?95175">www.vishay.com/doc?95175</a>
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